

## NPN General Purpose Amplifier

## **BCW71**

#### **Description**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 10.

#### **ABSOLUTE MAXIMUM RATINGS**

(T<sub>A</sub> = 25°C unless otherwise noted.) (Notes 1, 2)

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

#### THERMAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise noted.) (Note 3)

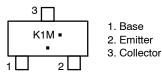
Symbol	Parameter	Max	Unit
$P_{D}$	Total Device Dissipation	350	mW
	Derate Above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

3. Device mounted on FR-4 PCB 40 mm x 40 mm x 1.5 mm.



SOT-23 CASE 318

#### **MARKING DIAGRAM**



(1 = Specific Device Code

M = Date Code ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping
BCW71	SOT-23 (Pb-Free, Halide Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

### **BCW71**

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted.)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0	45	_	_	V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0	50	-	_	V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0	5.0	-	-	V
I <sub>CBO</sub>	Collector Cut-Off Current	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C	- -	- -	100 10	μΑ
ON CHAR	ACTERISTICS					
h <sub>FE</sub>	DC Current Gain	$I_C$ = 2.0 mA, $V_{CE}$ = 5.0 V	110	_	220	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA	-	-	0.25	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 2.5 mA	-	0.85	_	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C$ = 2.0 mA, $V_{CE}$ = 5.0 V	0.6	-	0.75	V
SMALL SI	GNAL CHARACTERISTICS					
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C$ = 10 mA, $V_{CE}$ = 5.0 V, f = 35 MHz	-	330	_	MHz
C <sub>obo</sub>	Output Capacitance	V <sub>CE</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz	_	-	4.0	pF
C <sub>ibo</sub>	Input Capacitance	V <sub>EB</sub> = 0.5 V, I <sub>C</sub> = 0, f = 1.0 MHz	-	9.0	_	pF
NF	Noise Figure	$I_C$ = 0.2 mA, $V_{CE}$ = 5.0 V, $R_S$ = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz	_	-	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **BCW71**

#### **TYPICAL CHARACTERISTICS**

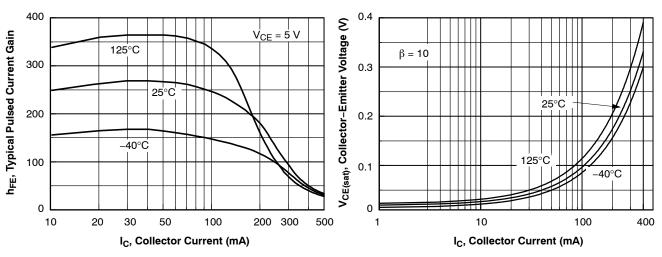


Figure 1. Typical Pulsed Current Gain vs. Collector Current

Figure 2. Collector–Emitter Saturation Voltage vs. Collector Current

**Collector Current** 

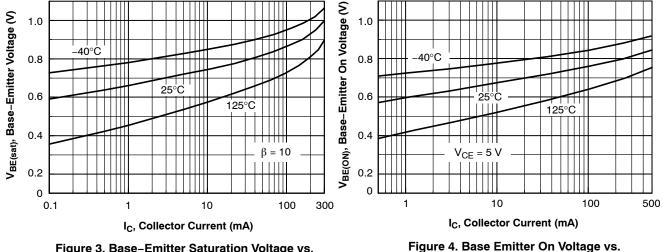


Figure 3. Base–Emitter Saturation Voltage vs.
Collector Current

100 100 f = 1.0 MHzV<sub>CB</sub> = 60 V I<sub>CBO</sub>, Collector Current (nA) 10 Capacitance (pF) 10  $C_{ib}$ 1 0.1 0.1 0.01 25 50 75 100 125 150 0.1 10 100 T<sub>A</sub>, Ambient Temperature (°C) V<sub>ce</sub>, Collector Voltage (V)

Figure 5. Collector Cut-Off Current vs.
Ambient Temperature

Figure 6. Input and Output Capacitance vs. Reverse Voltage

### **BCW71**

## TYPICAL CHARACTERISTICS (Continued)

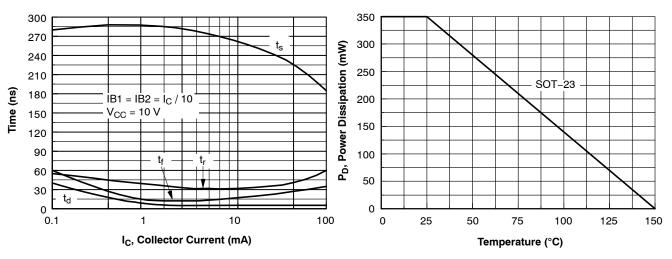


Figure 7. Switching Times vs. Collector Current

Figure 8. Power Dissipation vs. Ambient Temperature

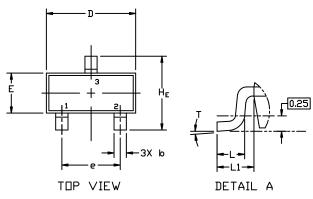


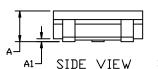


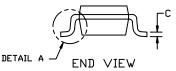
**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

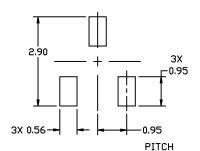
## GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



#### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2	

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales